(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
23 December 2010 (23.12.2010)

PCT

(10) International Publication Number
WO 2010/145907 A3

(51) International Patent Classification:
B81C 1/00 (2006.01)

(21) International Application Number:
PCT/EP2010/056947

(22) International Filing Date:
20 May 2010 (20.05.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

P200901282	20 May 2009 (20.05.2009)	ES
61/311,997	9 March 2010 (09.03.2010)	US
61/312,017	9 March 2010 (09.03.2010)	US
61/312,027	9 March 2010 (09.03.2010)	US
61/312,034	9 March 2010 (09.03.2010)	US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

[Continued on next page]

(54) Title: METHODS AND SYSTEMS FOR FABRICATION OF MEMS CMOS DEVICES

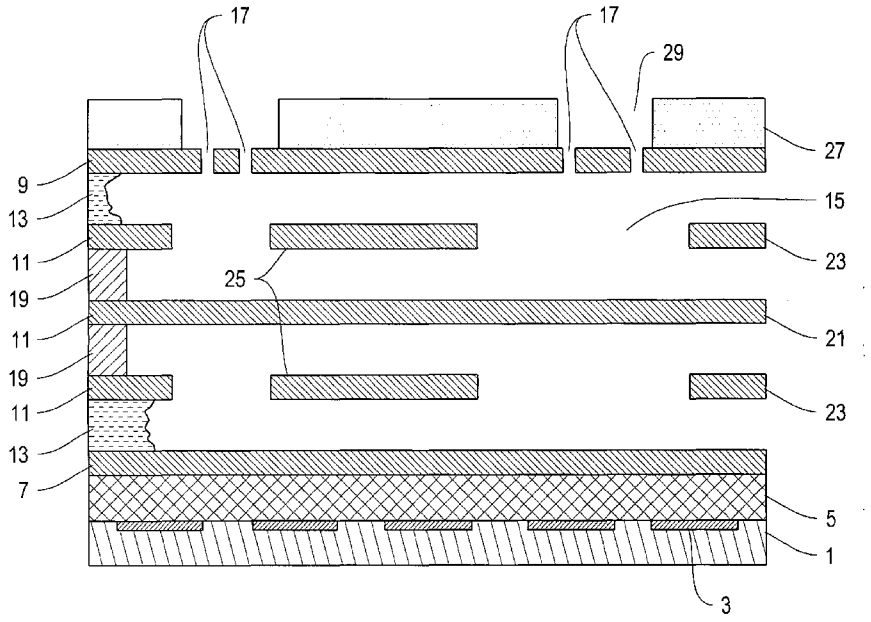


FIG. 1

(57) Abstract: A MEMS integrated circuit including a plurality of layers where a portion includes one or more electronic elements on a semiconductor material substrate. The circuit includes a structure of interconnection layers having a bottom layer of conductor material and a top layer of conductor material where the layers are separated by at least one layer of dielectric material. The bottom layer may be formed above and in contact with an Inter Dielectric Layer. The circuit also includes a hollow space within the structure of interconnection layers and a MEMS device in communication with the structure of interconnection layers.

WO 2010/145907 A3

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Published:

— *with international search report (Art. 21(3))*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

(88) Date of publication of the international search report:
19 May 2011